

L Number	Hits	Search Text	DB	Time stamp
1	6749	((372/10) or (372/11) or (372/14) or (372/15) or (372/16) or (372/43) or (372/75)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 11:04
2	19	((372/10) or (372/11) or (372/14) or (372/15) or (372/16) or (372/43) or (372/75)).CCLS.) and passive\$2 near10 q-switch\$3 and semiconductor and coat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 13:39
3	0	((372/10) or (372/11) or (372/14) or (372/15) or (372/16) or (372/43) or (372/75)).CCLS.) and graded adj2 ar adj coatings near4 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 13:40
4	0	((372/10) or (372/11) or (372/14) or (372/15) or (372/16) or (372/43) or (372/75)).CCLS.) and graded near4 ar adj coatings near4 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 13:40
5	0	((372/10) or (372/11) or (372/14) or (372/15) or (372/16) or (372/43) or (372/75)).CCLS.) and graded near4 coatings near4 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 13:41
6	1	graded near4 (antireflective or ar) adj2 coatings near4 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 13:42
7	1	graded near4 (antireflective or ar) adj2 coatings near4 (thick or thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 13:43
8	6585	graded adj index (antireflective or ar) adj2 coating	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 13:43
9	1	graded adj index adj (antireflective or ar) adj coating	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 14:31
10	6	graded near9 (antireflective or ar) adj coating same thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:10
11	2	("6215805").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:14
12	0	("66160824").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:15
13	2	("6160824").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:16
14	1	((tune or tuning) near12 q-switch\$3) near12 (translat\$3 or rotat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:46

15	0	rotation-induced near12 (tune or tuning) near12 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:47
16	0	translation-induced near12 (tune or tuning) near12 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:47
17	0	translation-induced near12 (tune or tuning) and q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:47
18	0	rotation-induced near12 (tune or tuning) and q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:47
19	87	rotat\$3 near12 (tune or tuning) and q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:48
20	43	(rotate or rotation) near12 (tune or tuning) and q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:48
21	7	(rotate or rotation) near12 (tune or tuning) and q-switch\$3 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 16:25
22	0	(rotate or rotation) near12 (tune or tuning) and passive\$2 near3 q-switch\$3 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 15:49
23	4	713436.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 16:30
24	4	semiconductor near2 passive\$2 near3 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 17:15
25	7	(infrared or ir) adj absorption near6 gaas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 17:43
26	4	(mqw or (multiple-quantum-well or multiple adj quantum adj well)) near3 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 18:24
28	0	(inp or algaas or indium adj phosphide or aluminum adj gallium adj arsenide) near12 q-switch\$3 near12 passive\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 18:26
27	5	(inp or algaas or indium adj phosphide or aluminum adj gallium adj arsenide) near12 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 20:42

29	0	(inp or algaas or indium adj phosphide or aluminum adj gallium adj arsenide) near12 q-switch\$3 and passive\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 18:26
30	3	("5015353").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 20:43
31	3	("4868834").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 20:43
-	243	q-switch.ti. and laser.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 09:41
-	215	q-switch.ti. and laser.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 10:17
-	2	q-switch.ti. and laser.ti. and (fabry-perot or f-p).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 11:05
-	31	passive adj (q-switch or q-switching) and semiconductor and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 11:15
-	6	passive adj (q-switch or q-switching).ti,ab. and semiconductor and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 11:16
-	3	passive adj (q-switch or q-switching).ti,ab. and semiconductor.ti,ab. and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 11:16
-	17	(US-6351478-\$ or US-6340806-\$ or US-6335942-\$ or US-3660777-\$ or US-6400495-\$ or US-5274650-\$ or US-5408480-\$ or US-5461637-\$ or US-5005176-\$ or US-5541948-\$).did. or (US-3660777-\$ or US-5541948-\$).did. or (US-6172997-\$ or US-6259711-\$ or US-6263004-\$ or US-6240113-\$ or US-6061378-\$).did.	USPAT; EPO; DERWENT	2002/07/13 11:17
-	0	(US-6351478-\$ or US-6340806-\$ or US-6335942-\$ or US-3660777-\$ or US-6400495-\$ or US-5274650-\$ or US-5408480-\$ or US-5461637-\$ or US-5005176-\$ or US-5541948-\$).did. or (US-3660777-\$ or US-5541948-\$).did. or (US-6172997-\$ or US-6259711-\$ or US-6263004-\$ or US-6240113-\$ or US-6061378-\$).did.	USPAT; EPO; DERWENT	2002/07/13 11:18
-	284	(372/10).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:18

-	157	(372/11).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:18
-	5180	(372/43).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:29
-	4	((372/11).CCLS.) and ((372/43).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:43
-	178	(passive or passively) near3 (q-switch or q-switching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:19
-	0	((372/11).CCLS.) and ((372/43).CCLS.) and ((passive or passively) near3 (q-switch or q-switching))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:19
-	95	semiconductor.ti,ab. and laser.ti,ab. and (q-switch or q-switching or passive\$2 near3 switch\$3) and 372/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:44
-	22	semiconductor.ti,ab. and laser.ti,ab. and (q-switch or q-switching or passive\$2 near3 switch\$3).ti,ab. and 372/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 15:36
-	5	semiconductor.ti,ab. and laser.ti,ab. and (q-switch or q-switching or passive\$2 near3 switch\$3).ti,ab. and 372/\$6.ccls. and passive	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 15:45
-	11	laser.ti,ab. and (q-switch or q-switching or passive\$2 near3 switch\$3).ti,ab. and 372/\$6.ccls. and (variable or vary) near4 wavelength	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 15:48
-	1	semiconductor adj laser and (passively or passive) adj (q-switch or q-switching) and (variable or vary or varies) near3 (wavelength or frequency or frequencies)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:02
-	157	(372/11).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:02
-	43	((372/11).CCLS.) and semiconductor near3 (laser or q-switch)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:03
-	0	((372/11).CCLS.) and semiconductor near3 (laser or q-switch)) and q-switch near4 (tune or variable) near4 (wavelength or frequency)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:04
-	0	((372/11).CCLS.) and semiconductor near3 (laser or q-switch)) and q-switch near12 (tune or variable) near12 (wavelength or frequency)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:04

-	15	((372/11).CCLS.) and semiconductor near3 (laser or q-switch)) and ((tune or tuning) near12 (wavelength or frequency))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:04
-	5578	((372/10).CCLS.) or ((372/11).CCLS.) or ((372/43).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:30
-	0	((372/10).CCLS.) or ((372/11).CCLS.) or ((372/43).CCLS.) and (coated or coating) near12 (reflector or reflecting or reflect) near12 thickness near12 (infrared or infra-red or IR) and (Q-switch or Q-switching) near12 (passive or passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:33
-	0	((372/10).CCLS.) or ((372/11).CCLS.) or ((372/43).CCLS.) and (coated or coating or coat) near12 (reflector or reflecting or reflect) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:34
-	0	((372/10).CCLS.) or ((372/11).CCLS.) or ((372/43).CCLS.) and (layer or film or cover or covering or coated or coating or coat) near12 (reflector or reflecting or reflect) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:35
-	0	(layer or film or cover or covering or coated or coating or coat) near12 (reflector or reflecting or reflect) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:35
-	27	(layer or film or cover or covering or coated or coating or coat) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:36
-	14	(layer or film or cover or covering or coated or coating or coat) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively) and semiconductor near12 laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:13
-	18	(layer or film or cover or covering or coated or coating or coat) near12 (thick or thickness) and Q-switch\$3 near12 (passive or passively) and semiconductor near12 laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:13
-	4	((layer or film or cover or covering or coated or coating or coat) near12 (thick or thickness) and Q-switch\$3 near12 (passive or passively) and semiconductor near12 laser) not ((layer or film or cover or covering or coated or coating or coat) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively) and semiconductor near12 laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:27
-	1	ar adj coating near12 (gradient or variable or graded or non-uniform or nonuniform) and q-switch\$3 near12 semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:33
-	1	coating near12 (gradient or variable or graded or non-uniform or nonuniform) and passive\$2 near12 q-switch\$3 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:35

-	1	graded near12 coating and passive\$2 near12 q-switch\$3 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:36
-	1	graded near12 coat\$3 and passive\$2 near12 q-switch\$3 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:36
-	5	ar near12 coat\$3 and passive\$2 near12 q-switch\$3 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:53
-	2	("6215805").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 19:11
-	0	("modulat\$3 near12 (thickness or coat\$3) near12 q-switch\$3").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 19:11
-	3	modulat\$3 near12 (thickness or coat\$3) near12 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 19:15
-	1	modulat\$3 near12 (ar or anti-reflective or antireflective) near12 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 19:15